June 2008

TLE4946-2L

High Precision Hall Effect Latch

TLE4946-2L

Datasheet

Rev 1.0

Sensors



Never stop thinking

Edition 2008-06

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TLE4946-2L High Precision Hall Effect Latch

Revision History: 2008-06, Rev 1.0

Previous Version:						
Page	Subjects (major changes since last revision)					

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High Precision Hall Effect Latch

TLE4946-2L

1 **Product Description**

1.1 Overview

The TLE4946-2L is a high precision Hall effect latch with highly accurate switching thresholds for operating temperatures up to 150°C.

1.2 Features

- 2.7 V to 18 V supply voltage operation
- Operation from unregulated power supply
- High sensitivity and high stability of the magnetic switching points
- · High resistance to mechanical stress by active error compensation
- Reverse battery protection (V_s = -18V)
- Superior temperature stability
- Peak temperatures up to 195°C without damage
- Low jitter (typ. 1µs)
- High ESD performance (± 4 kV HBM)
- Digital output signal

1.3 Target Applications

The TLE4946-2L is an integrated circuit Hall-effect sensor with low switching thresholds and low hysteresis. It is specially designed for high sensitivity applications and is ideally suited to detect the rotor position in a BLDC motor. Also for index counting with small pole wheels and large air gaps the sensor provides a reliable switching information.

2 Functional Description

2.1 General

Precise magnetic switching thresholds and high temperature stability are achieved by active compensation circuits and chopper techniques on chip. Offset voltages, generated by temperature induced stress or overmolding are canceled and high accuracy is achieved. The IC has an open collector output stage with 20mA current sink capability. A wide operating voltage range form 2.7V to 18V with reverse polarity protection up to -18V makes the device suitable for a wide range of applications. A magnetic south pole with field strength above B_{op} turns the output on and a magnetic north pole exceeding B_{rp} turns it off.

Product Name	Product Type	Ordering Code	Package	
Hall Effect Latch	TLE4946-2L	SP000398352	PG-SSO-3-2	





Functional Description

2.2 Pin Configuration

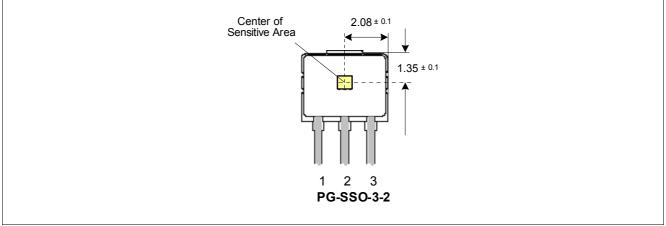


Figure 1 Pin Configuration and sensitive area (Top View, Figure not to Scale)

2.3 Pin Description

Table 1 Pin Description								
Pin or Ball	Name	Pin	Function	Comments				
No.		Туре						
1	Vs	I	Supply voltage					
2	GND	0	Ground					
3	Q	0	Output					

2.4 Block Diagram

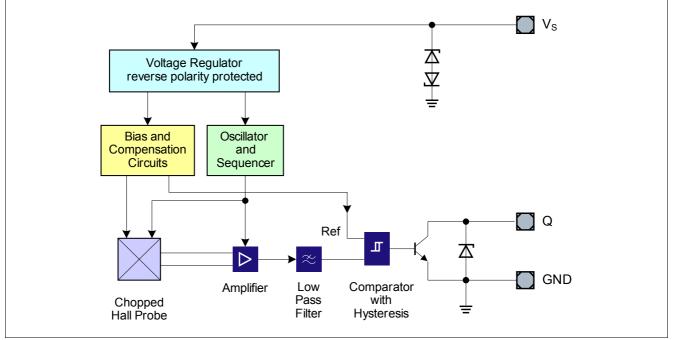


Figure 2 TLE4946-2L Block Diagram

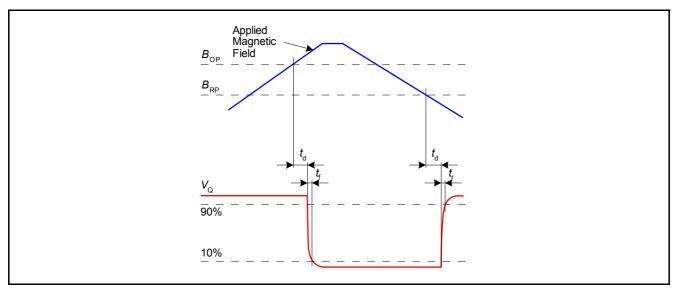


Functional Description

2.5 Operating Modes and States

Field Direction Definition:

Positive magnetic fields are related with the south pole of the magnet to the branded side of package.





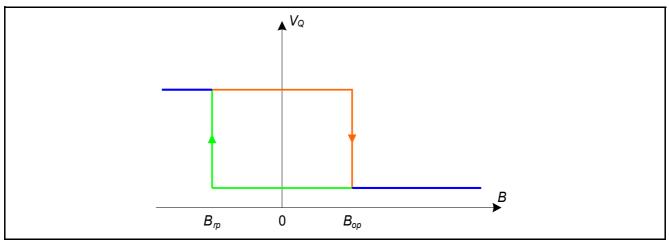


Figure 4 Output Signal

2.6 Functional Block Description

The chopped Hall IC switch comprises a Hall probe, bias generator, compensation circuits, oscillator and output transistor.

The bias generator provides currents for the Hall probe and the active circuits. Compensation circuits stabilize the temperature behavior and reduce technology variations.

The Active Error Compensation rejects offsets in signal stages and the influence of mechanical stress to the Hall probe caused by molding and soldering processes and other thermal stresses in the package.

This chopper technique together with the threshold generator and the comparator ensure high accurate magnetic switching points



Specification

3 Specification

3.1 Application Circuit

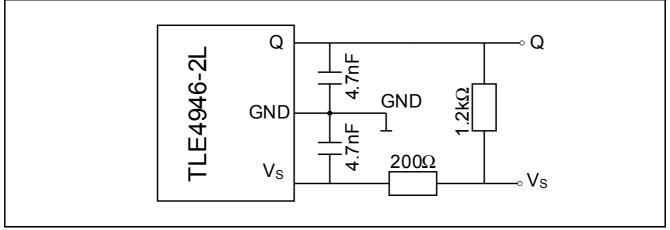


Figure 5 Application circuit

It is recommended to use a serial resistor of 200Ω in the supply line for current limitation in the case of a overvoltage pulse. Two capacitors of 4.7nF enhance the EMC performance. The pull-up resistor of $1.2k\Omega$ limits the current through the output transistor.

3.2 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Тур.	Max.	-	
Max. junction temperature	T _J	-40	-	150	°C	
		-	-	155		for 2000 h (not additive)
		_	-	165		for 1000 h (not additive
		_	-	175		for 168 h (not additive)
		_	-	195		for 3 x 1 h (additive)
Supply voltage	V _{DD}	-18 -18 -18		18 24 26	V	for 1h, $R_{\rm s} \ge 200\Omega$ for 5min, $R_{\rm s} \ge 200\Omega$
Supply current through protection device	I _S	- 50	-	+ 50	mA	
Output voltage	V _Q	-0.7	-	18	V	
		-0.7	-	26		for 5min @ 1.2k Ω pull up
Storage temperature	T _S	- 40	-	150	°C	
Magnetic flux density	В		-	unlimited	mT	
ESD robustness HBM: 1.5 kΩ, 100 pF	$V_{\rm ESD,HBM}$	4			kV	According to EIA/JESD22-A114-B



Attention: Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

3.3 Operating Range

The following operating conditions must not be exceeded in order to ensure correct operation of the TLE4946-2L. All parameters specified in the following sections refer to these operating conditions unless otherwise mentioned.

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Тур.	Max.		
Supply voltage	Vs	2.7	-	18	V	
Output voltage	VQ	- 0.7	-	18	V	
Junction temperature	Ti	- 40	-	150	°C	
Output current	I _Q	0	-	20	mA	

Table 3 Operating Range

3.4 Characteristics

Product characteristics involve the spread of values guaranteed within the specified voltage and ambient temperature range. Typical characteristics are the median of the production (at $V_s = 12V$ and $T_A = 25^{\circ}C$).

Table 4 Electrical Characteristics

Symbol	Values			Unit	Note/ Test Condition
	Min.	Тур.	Max.		
Is	2	4	6	mA	V _S = 2.7 V 18 V
I _{SR}	0	0.2	1	mA	V _S = - 18 V
V _{QSAT}	_	0.3	0.6	V	I _Q = 20 mA
I _{QLEAK}	_	0.05	10	μA	for V _Q = 18 V
t _f	_	0.02	1	μs	$R_{\rm L}$ = 1.2 kΩ;
<i>t</i> _r	_	0.4	1	μs	C _L = 50 pF
fosc	_	320	-	kHz	
f _{sw}	0	-	15 ¹⁾	kHz	
t _d	_	13	-	μs	
t _{QJ}	-	1	-	μs _{RMS}	Typ. value for square wave signal 1 kHz
t _{PON}	-	13	-	μs	V _S ≥2.7 V
R _{thJA}	-		190	K/W	PG-SSO-3-2
	I_{S} I_{SR} V_{QSAT} I_{QLEAK} t_{f} t_{r} f_{OSC} f_{SW} t_{d} t_{QJ} t_{PON}	$\begin{tabular}{ c c c c c } \hline Min. \\ \hline I_S & 2 \\ \hline I_{SR} & 0 \\ \hline V_{QSAT} & - \\ \hline I_{QLEAK} & - \\ \hline t_f & - \\ \hline t_f & - \\ \hline t_r & - \\ \hline f_{OSC} & - \\ \hline f_{OSC} & - \\ \hline f_{SW} & 0 \\ \hline t_d & - \\ \hline t_{QJ} & - \\ \hline t_{PON} & - \\ \hline \end{tabular}$	Min. Typ. $I_{\rm S}$ 2 4 $I_{\rm SR}$ 0 0.2 $V_{\rm QSAT}$ - 0.3 $I_{\rm QLEAK}$ - 0.05 $t_{\rm f}$ - 0.02 $t_{\rm GSC}$ - 320 $f_{\rm SW}$ 0 - $t_{\rm d}$ - 13 $t_{\rm QJ}$ - 13	Min. Typ. Max. $I_{\rm S}$ 2 4 6 $I_{\rm SR}$ 0 0.2 1 $V_{\rm QSAT}$ - 0.3 0.6 $I_{\rm QLEAK}$ - 0.05 10 $t_{\rm f}$ - 0.02 1 $t_{\rm f}$ - 0.05 10 $t_{\rm f}$ - 0.02 1 $t_{\rm GSC}$ - 320 - $f_{\rm SW}$ 0 - 15 ¹ $t_{\rm d}$ - 13 - $t_{\rm QJ}$ - 13 - $t_{\rm PON}$ - 13 -	Min. Typ. Max. I_S 2 4 6 mA I_{SR} 0 0.2 1 mA V_{QSAT} - 0.3 0.6 V I_{QLEAK} - 0.02 1 μA t_{f} - 0.05 10 μA t_{f} - 0.02 1 μS f_{OSC} - 0.4 1 μS f_{OSC} - 320 - kHz f_{SW} 0 - 15 ¹ kHz t_{d} - 13 - μS_{RMS} t_{QJ} - 13 - μS_{RMS}

1) To operate the sensor at the max. switching frequency, the value of the magnetic signal amplitude must be 1.4 times higher than for static fields.

This is due to the - 3 dB corner frequency of the low pass filter in the signal path.

2) Systematic delay between magnetic threshold reached and output switching

3) Jitter is the unpredictable deviation of the output switching delay

4) Time from applying $V_{\rm S} \ge 2.7$ V to the sensor until the output state is valid

5) Thermal resistance from junction to ambient



Package Information

Table 5 Magnetic Characteristics

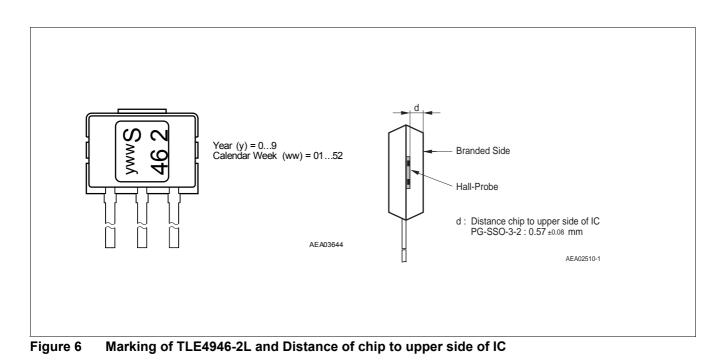
Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Тур.	Max.		
Operate point	B _{OP}	0.5	2.0	3.5	mT	
Release point	B _{RP}	-3.5	-2.0	-0.5	mT	
Hysteresis	B _{HYS}	1.0	4	6.0	mT	
Magnetic Offset ¹⁾	B_{OFF}	-1.5	0	1.5	mT	
Temperature compensation of magn. thresholds	тс		-350		ppm/°C	
Repeatability of magnetic thresholds ²⁾	B _{REP}		20		μT_{RMS}	

1) $B_{off} = (B_{op} + B_{rp})/2$

2) B_{REP} is equivalent to the noise constant

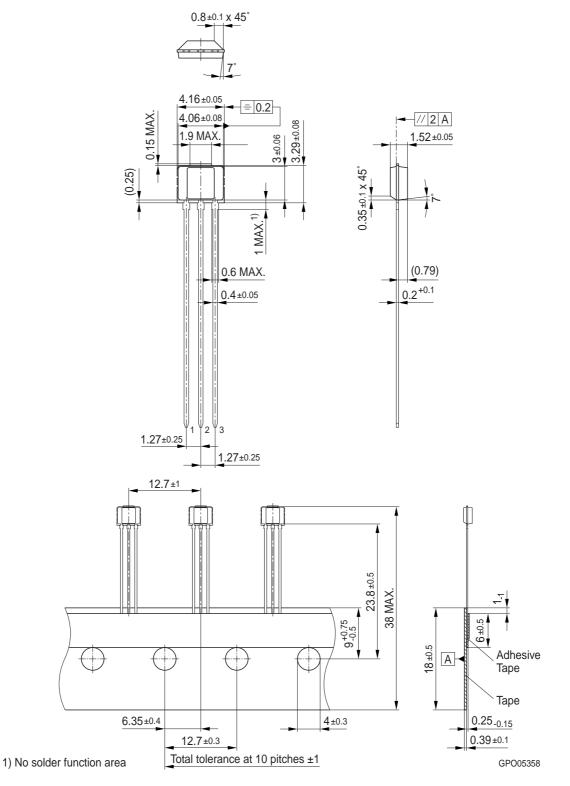
4 Package Information

4.1 Package Outline





Package Information





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